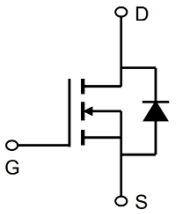
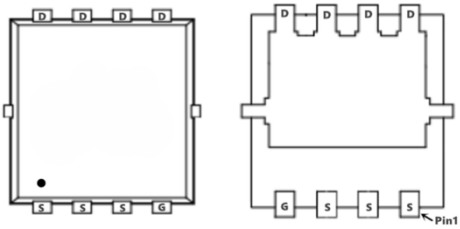
LM3D60N03

30V N-Channel Enhancement Mode MOSFET

Description

The LM3D60N03 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.





General Features

V_{DS} = 30V I_D =60A

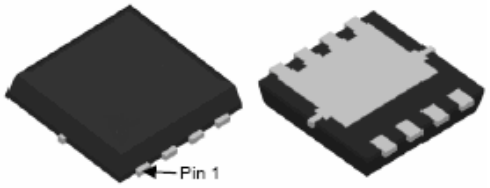
$R_{DS(ON)}$ < 8.5mΩ @ V_{GS}=10V

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LM3D60N03	AP60N03DF	DFN3.3X3.3	-	-	5000 units

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	60	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	29	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	11	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	9	A
I_{DM}	Pulsed Drain Current[2]	92	A
EAS	Single Pulse Avalanche Energy[3]	57.8	mJ
I_{AS}	Avalanche Current	34	A
P_D@T_C=25℃	Total Power Dissipation[4]	29	W
P_D@T_A=25℃	Total Power Dissipation[4]	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	75	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	4.32	℃/W

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
△BVDSS/△TJ	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.027	---	V/℃
RDS(ON)	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=12A	---	7	8.5	mΩ
		V_{GS}=4.5V , I_D=10A	---	10	13	
VGS(th)	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	---	2.5	V
△VGS(th)	$V_{GS(th)}$ Temperature Coefficient		---	-5.8	---	mV/℃
IDSS	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=24V , V_{GS}=0V , T_J=55℃	---	---	5	
IGSS	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=15A	---	9.8	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=12A	---	12.8	---	nC
Qgs	Gate-Source Charge		---	3.3	---	
Qgd	Gate-Drain Charge		---	6.5	---	
Td(on)	Turn-On Delay Time	V_{DD}=12V , V_{GS}=10V , R_G=3.3Ω I_D=5A	---	4.5	---	ns
T_r	Rise Time		---	10.8	---	
Td(off)	Turn-Off Delay Time		---	25.5	---	
T_f	Fall Time		---	9.6	---	
Ciss	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1317	---	pF
Coss	Output Capacitance		---	163	---	
Crss	Reverse Transfer Capacitance		---	131	---	
IS	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	46	A
ISM	Pulsed Source Current[2,6]		---	---	92	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :

1、The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=34A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics

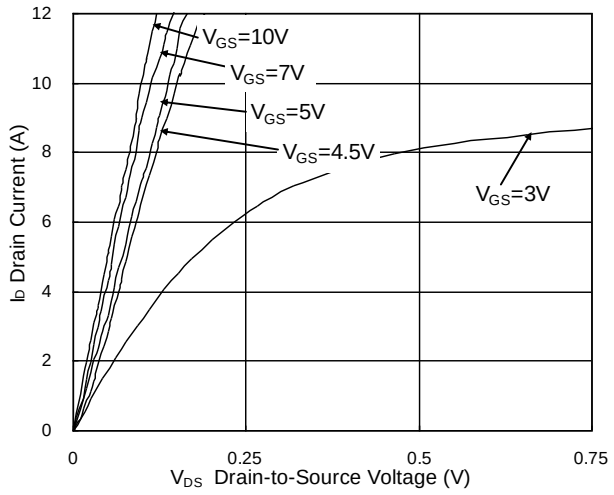


Fig.1 Typical Output Characteristics

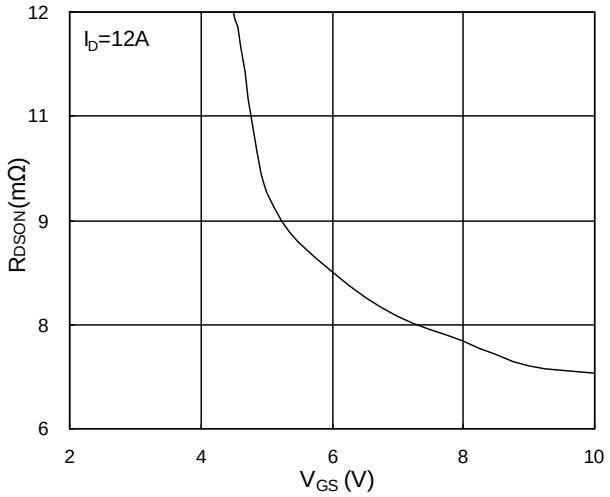


Fig.2 On-Resistance vs. G-S Voltage

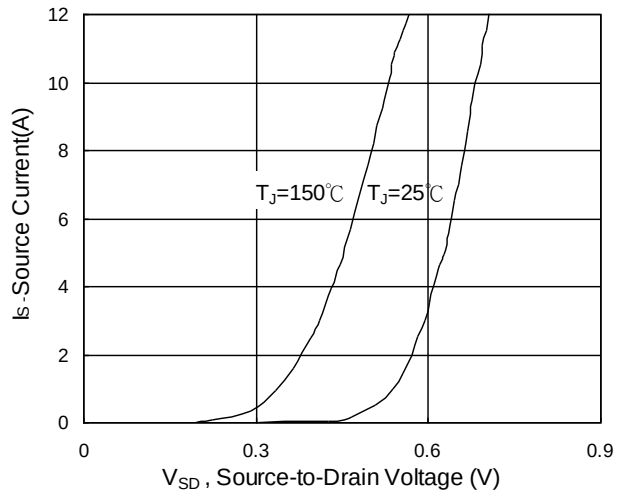


Fig.3 Forward Characteristics of Reverse

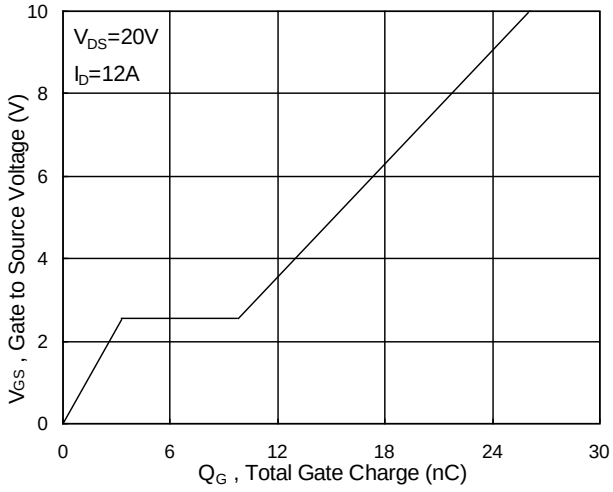


Fig.4 Gate-Charge Characteristics

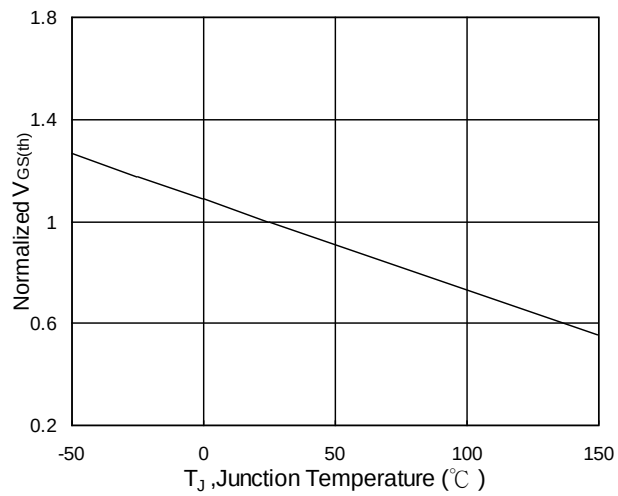


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

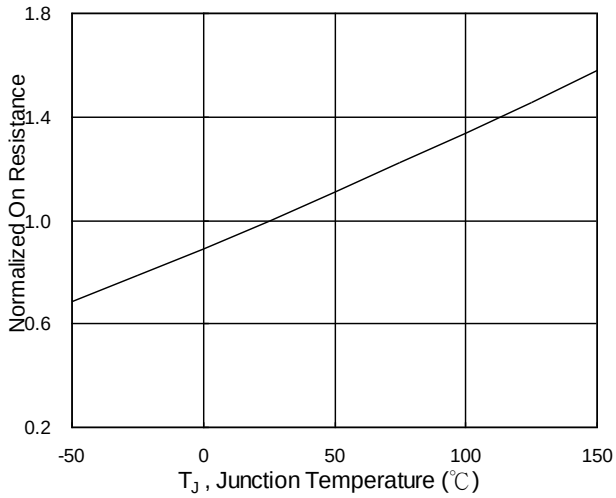


Fig.6 Normalized R_{DSON} vs. T_J

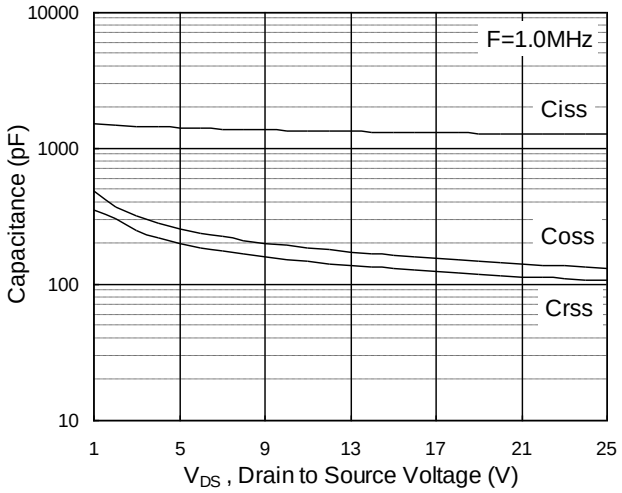


Fig.7 Capacitance

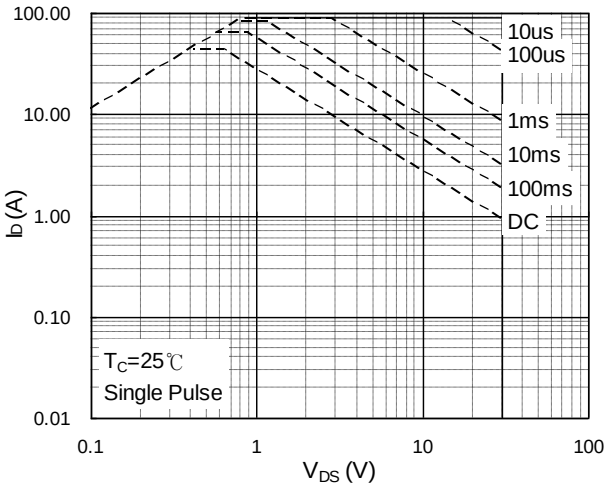


Fig.8 Safe Operating Area

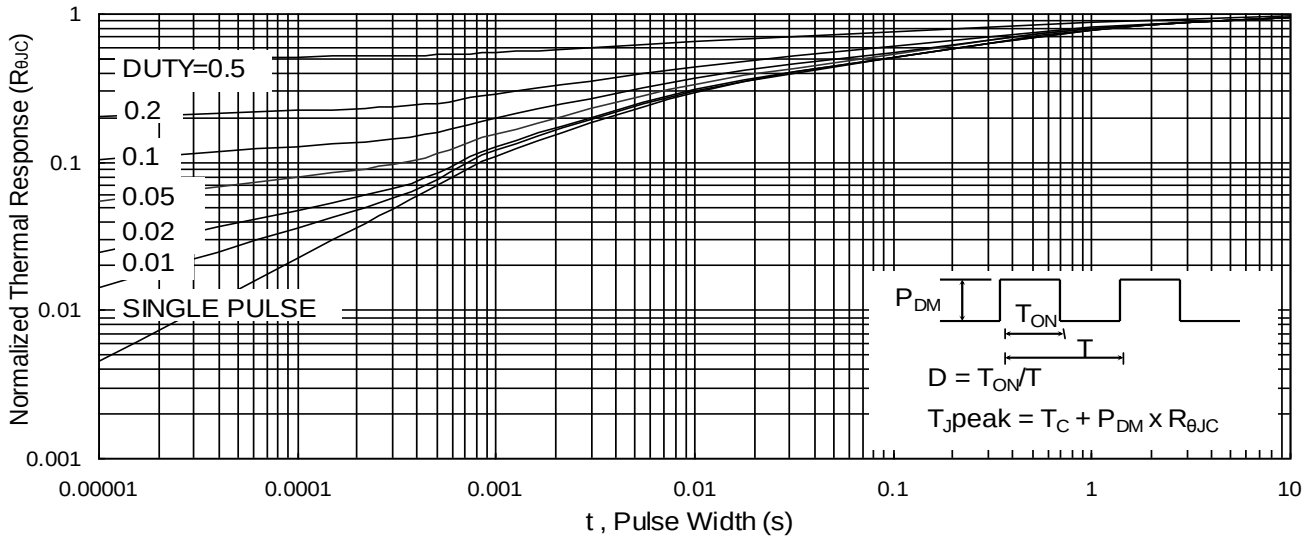


Fig.9 Normalized Maximum Transient Thermal Impedance

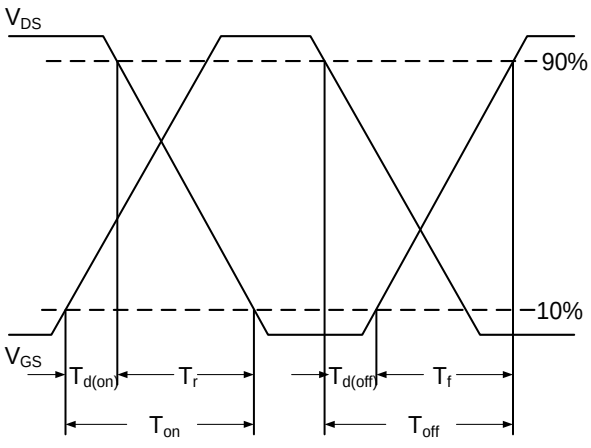


Fig.10 Switching Time Waveform

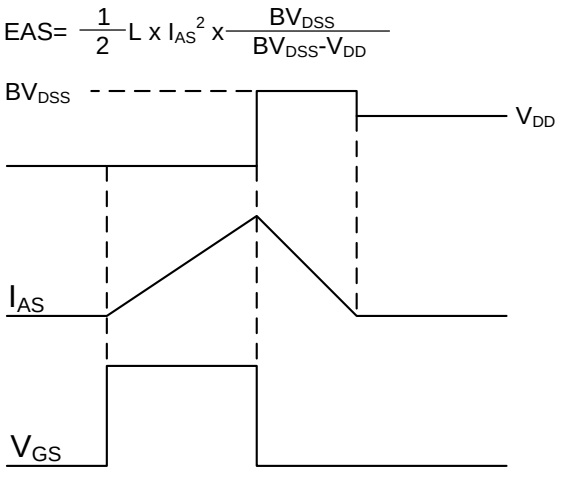
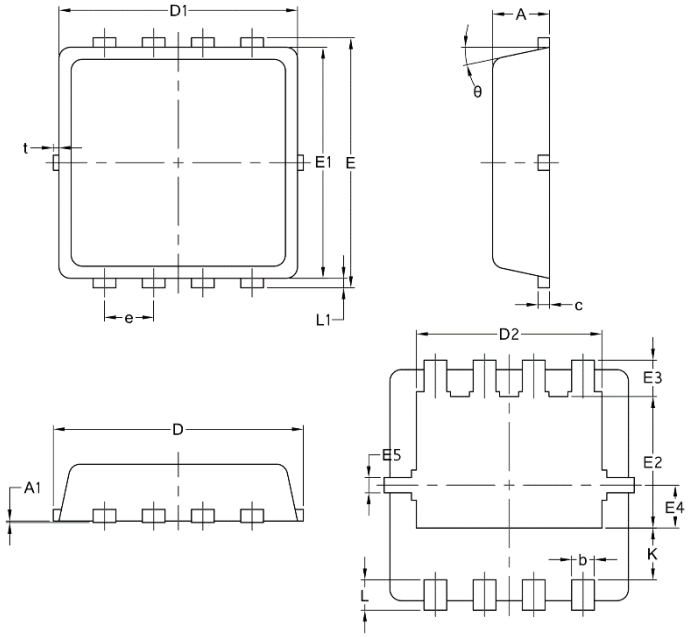


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data-DFN3*3-JQ Single



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14

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